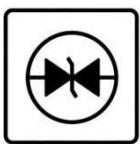




ESD



TVS



TSS



MOV



GDT



PLED

PC817x-MS

产品手册

特征

- 电流转换比(CTR: 最小 50% 工作条件 $I_F=5mA$, $V_{CE}=5V$)
- 绝缘电压: ($V_{ISO}=5,000V_{rms}$)
- 响应时间 (tr: TYP. 6 μs ; tf: TYP. 5 μs)工作条件 $V_{CE}=2V$, $I_C=2mA$, $R_L=100 \Omega$)
- ESD : HBM8000V&MM2000V

说明

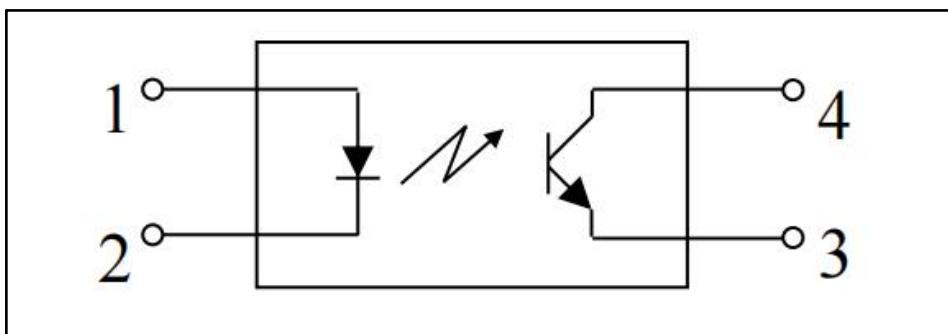
- PC 817 系列光耦合器的组成是: 由一个 GaAs 的发射管和一个 NPN 的晶体管组成;
- PC 817 的引脚中心距是 2.54mm;

应用范围

- 开关电源.
- 贮存器, 复印机, 自动售货机.
- 电表.
- 家用电器, 如风扇等.
- 电脑.
- 信号传输系统.
- 器具的应用, 测量机.

参考信息

封装	丝印
	 <p>● PC817 X***</p>
DIP-4	<p>说明: 印字中的“x”代表产品 CTR 分档: A、B、C、D 等; ***代表批次号;</p>
	
SOP-4	

框架结构

最大绝对额定值 (常温=25℃)

参数 Parameter		符号 Symbol	额定值 Rated Value			单位 Unit		
输入 Inout	顺向电流 Forward Current	I _F	50			mA		
	逆向电压 Reverse Voltage	V _R	6			V		
	功耗率 Consume Power	P	70			mW		
输出 Output	集极与射极电压 Collector and emitter Voltage	V _{CEO}	35		V			
	射极与集极电压 Emitter and collector Voltage	V _{ECO}	6					
	集极电流 Collector Current	I _C	50			mA		
	消耗功率 Consume Power	P _C	150			mW		
总功率消耗 Total Consume Power		P _{tot}	200			mW		
*1 绝缘电压 Insulation Voltage		V _{iso}	5,000			Vrms		
最大绝缘电压 Max Insulation Voltage		V _{IOTM}	6,000			V		
额定脉冲绝缘电压 Rated Impulse Insulation Voltage		V _{IORM}	630			V		
工作温度 Working Temperature		T _{opr}	-55 to + 110		°C			
存贮温度 Deposit Temperature		T _{stg}	-55 to + 125					
*2 焊锡温度 Soldering Temperature		T _{sol}	260					

*1. 交流测试，时间 1 分钟，湿度 = 40~60% AC Test, 1 minute, humidity = 40~60%

如下是绝缘测试的方法。Insulation test method as below:

- (1) 将产品的两端短路。 Short circuit both terminals of photocoupler
- (2) 测试绝缘电压时无电流通过。 No Current when testing insulation voltage
- (3) 测试时加正弦波形电压。 Adding sine wave voltage when testing

*2. 锡焊时间为 10 秒 soldering time is 10 seconds

光电特性 (常温=25℃)

参数 Parameter		符号 Symbol	条件 Condition	最小 Min	中.Mid ium	最大 Max	单位 Unit
输入 Input	顺向电压 Forward Current	V _F	I _F =20mA	---	1.20	1.40	V
	逆向电流 Reverse Voltage	I _R	V _R =5V	---	---	5	uA
	集极电容 Collector capacitance	C _t	V=0, f=1MHz	---	30	250	pF
输出 Output	集 极 至 射 极 电 流 Collector to emitter Current	I _{CEO}	V _{CE} =70V, I _F =0mA	---	---	150	nA
	集 极 与 射 极 衰 减 电 压 Collector and Emitter attenuation Voltage	BV _{CEO}	I _C =0. 1mA I _F =0mA	70	---	---	V
	射 极 与 集 极 衰 减 电 压 Emitter and Collector attenuation Voltage	BV _{ECO}	I _E =10μA I _F =0mA	6	---	---	V

传输特性 Transforming Characteristics	*1 电流转换比 Current conversion ratio	CTR	IF=5mA VCE=5V	50	---	600	%
	集极与射极饱和电压 Collector and Emitter Saturation Voltage	V _{CE(sat)}	I _F =20m A I _c =1mA	---	0.1	0.2	V
	绝缘阻抗 Insulation Impedance	R _{iso}	DC500V 40~60%R.H.	5×10 ¹⁰	1×10 ¹¹	---	Ω
	电容量 capacitance	C _f	V=0, f=1MHz	---	0.6	1	pF
	转换频率 Transforming Frequency	f _c	V _{CE} =5V, I _c =2mA R _L =100Ω, -3dB	---	80	---	kHz
	上升时间 Rise time	t _r	V _{CE} =2V, I _c =2mA R _L =100Ω	---	6	18	μs
	下降时间 Descend Time	t _f		---	5	18	μs

电流转换比 Current Conversion Ratio = IC / IF × 100%

电流转换比的等级分类 Grades of Current conversion ratio

等级标示 Grade Sign	最小. Min (%)	最大. Max (%)
A	100	160
B	130	260
C	200	400
D	300	600
A or B or C or D	50	600

说明 : 工作条件: I_F=5mA, V_{CE}=5V, T_a=25°C.

Note: Working condition: I_F=5mA, V_{CE}=5V, T_a=25°C.

RATING AND CHARACTERISTIC CURVES (PC817)

Fig.1 Forward Current
vs. Ambient Temperature

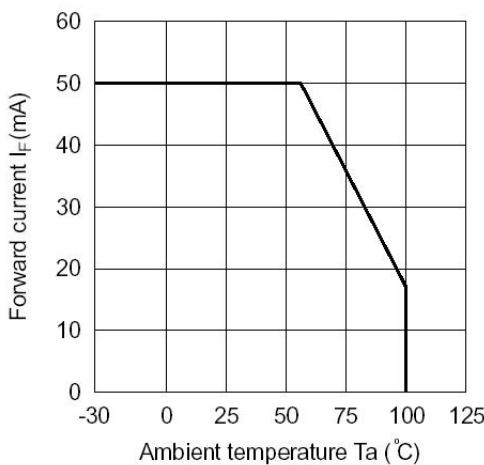


Fig.2 Collector Power Dissipation
vs. Ambient Temperature

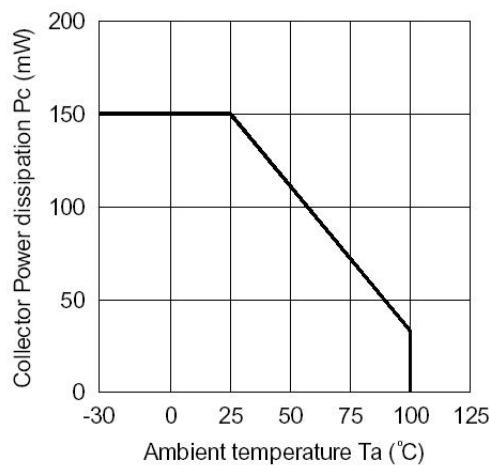


Fig.3 Collector-emitter Saturation
Voltage vs. Forward Current

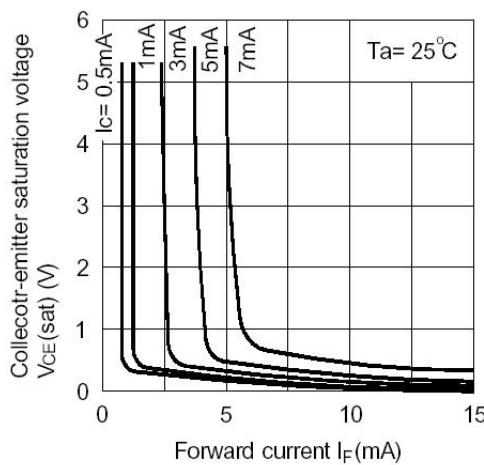


Fig.4 Forward Current vs. Forward
Voltage

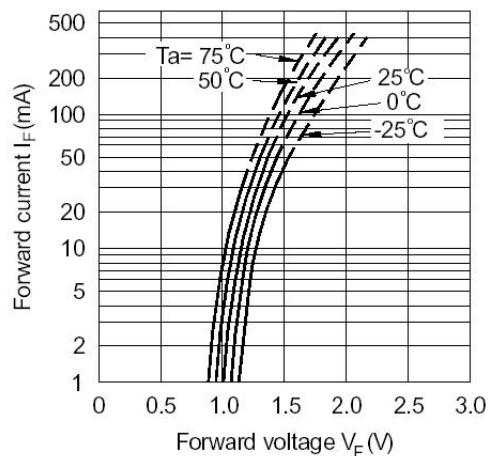


Fig.5 Current Transfer Ratio vs.
Forward Current

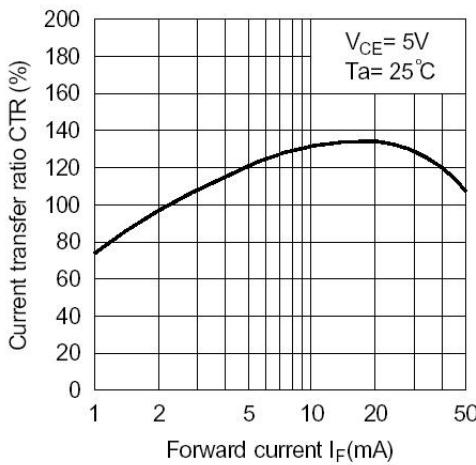
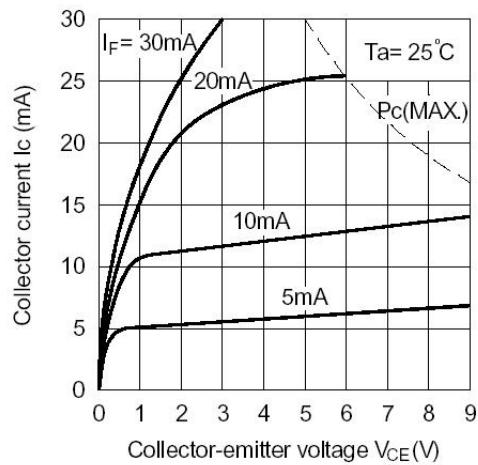


Fig.6 Collector Current vs.
Collector-emitter Voltage



RATING AND CHARACTERISTIC CURVES (PC817)

Fig.1 Forward Current
vs. Ambient Temperature

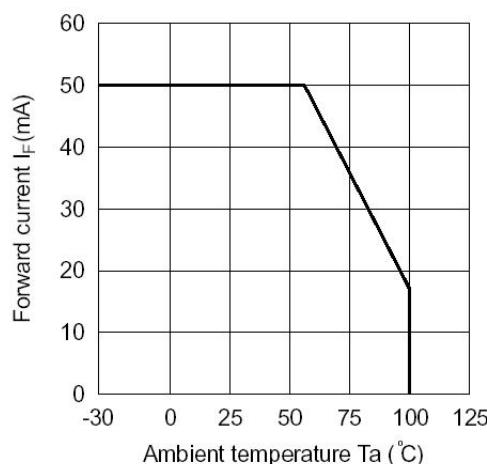


Fig.2 Collector Power Dissipation
vs. Ambient Temperature

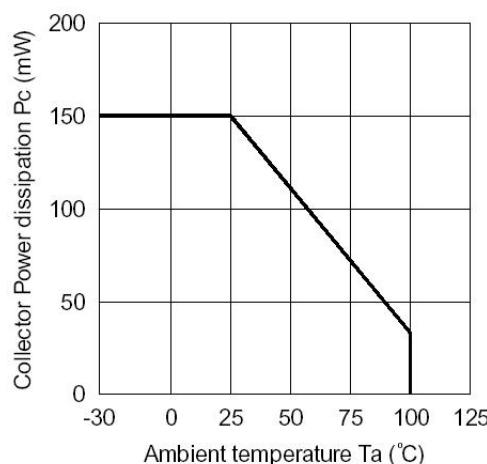


Fig.3 Collector-emitter Saturation
Voltage vs. Forward Current

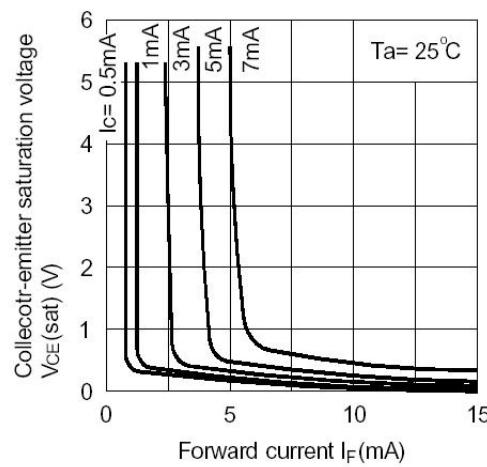


Fig.4 Forward Current vs. Forward
Voltage

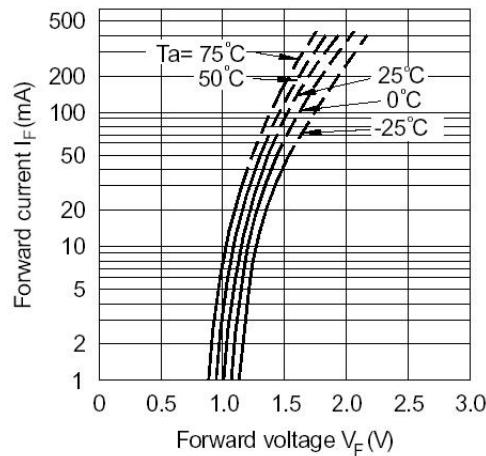


Fig.5 Current Transfer Ratio vs.
Forward Current

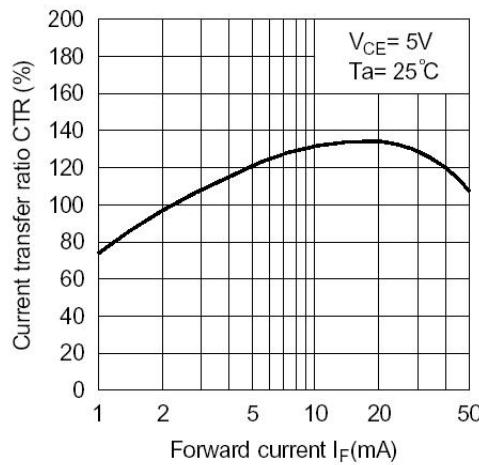
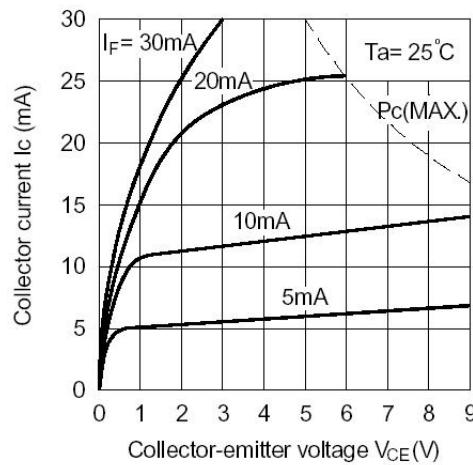


Fig.6 Collector Current vs.
Collector-emitter Voltage



RATING AND CHARACTERISTIC CURVES (PC817)

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

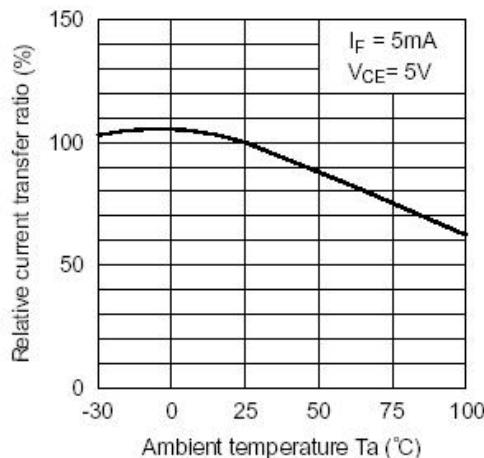


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

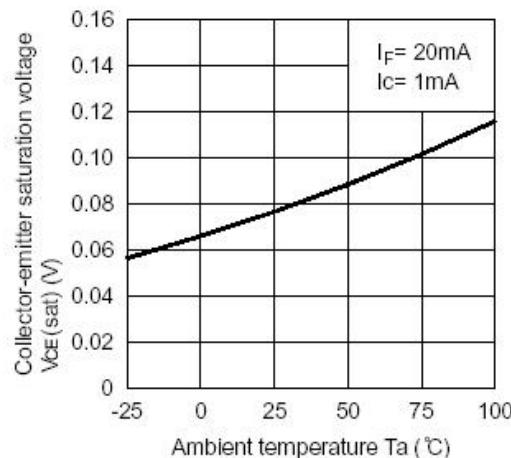


Fig.9 Collector Dark Current vs. Ambient Temperature

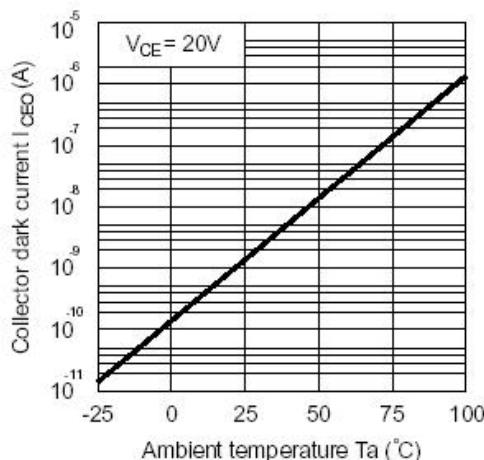


Fig.10 Response Time vs. Load Resistance

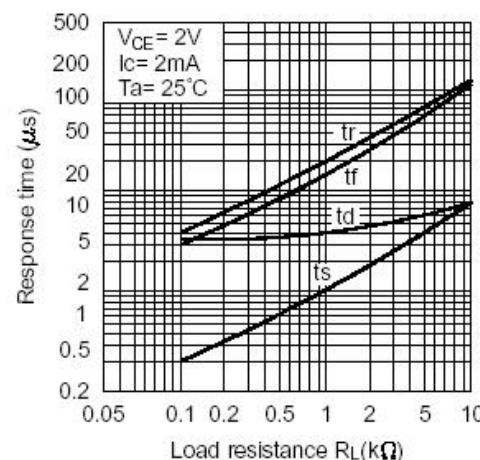
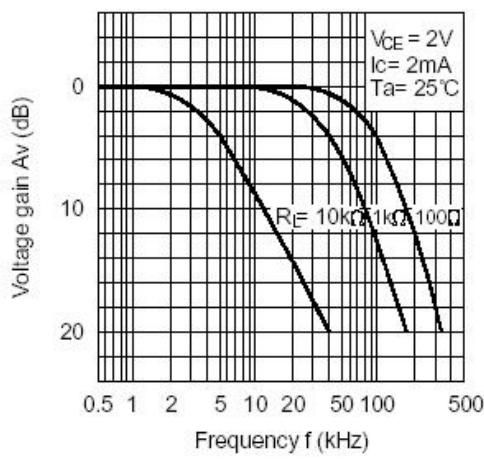
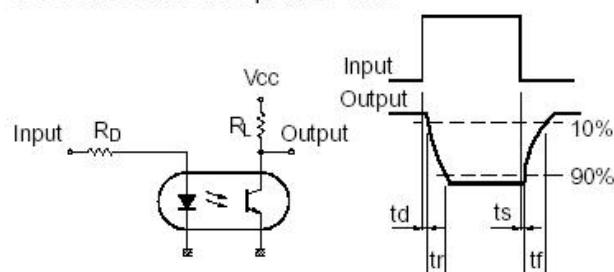


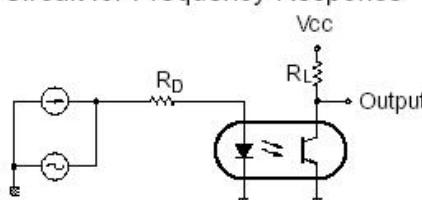
Fig.11 Frequency Response



Test Circuit for Response Time

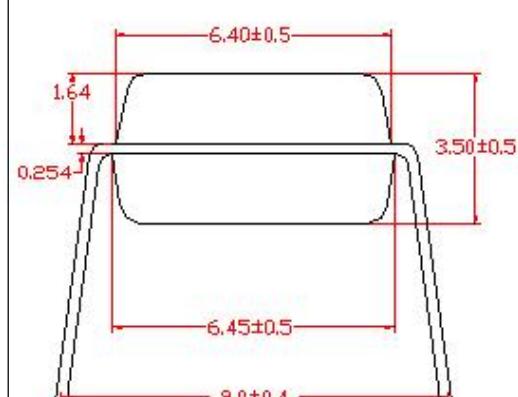
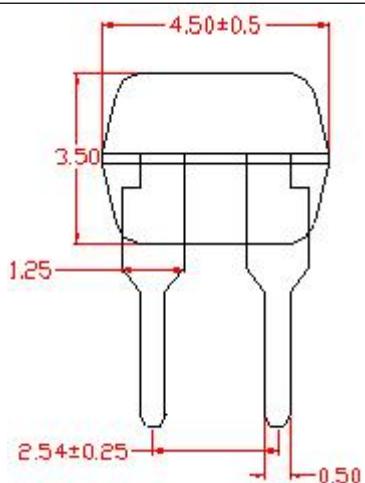
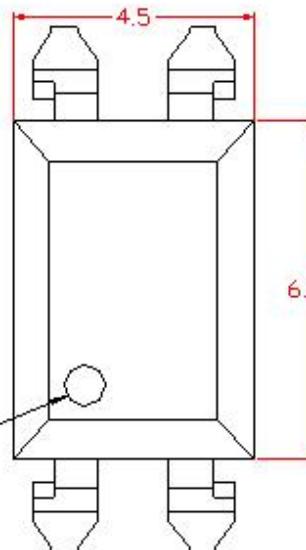


Test Circuit for Frequency Response

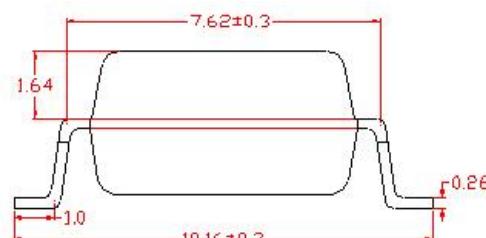
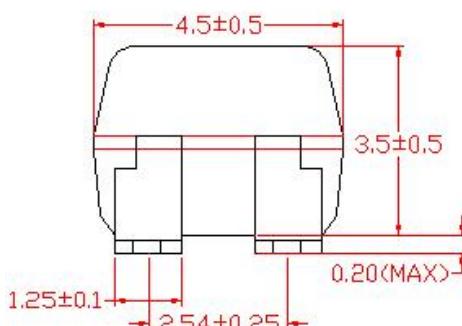
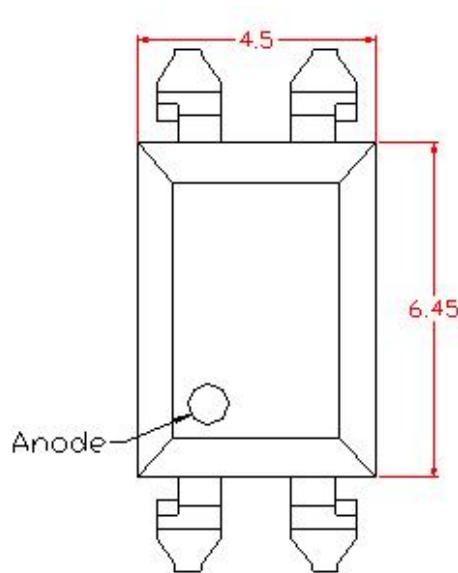


外形尺寸

Unit: mm (inch)



DIP-4



SOP-4

产品订购信息

产品名称	封装	包装	最小包装	包装数量
PC817X-MS	DIP-4	管装	100PCS/管	1000PCS/盒
PC817X-MS	SOP-4	卷盘	2000PCS/盘	10000PCS/盒

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